

The documentation and process conversion measures necessary to comply with this revision shall be completed by 14 October 2016.

INCH-POUND

MIL-PRF-19500/760A  
14 July 2016  
SUPERSEDING  
MIL-PRF-19500/760  
30 March 2011

PERFORMANCE SPECIFICATION SHEET

TRANSISTOR, FIELD EFFECT RADIATION HARDENED, N-CHANNEL, SILICON, ENCAPSULATED (SURFACE MOUNT PACKAGE), TYPES 2N7579, 2N7581, 2N7583, AND 2N7585, JANTXV, AND JANS

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of this specification sheet and [MIL-PRF-19500](#).

1. SCOPE

1.1 Scope. This specification covers the performance requirements for a N-channel, enhancement-mode, MOSFET, radiation hardened (total dose and single event effects (SEE)), power transistor. Two levels of product assurance (JANTXV and JANS) are provided for each encapsulated device, with avalanche energy maximum rating ( $E_{AS}$ ) and maximum avalanche current ( $I_{AS}$ ). Provisions for radiation hardness assurance (RHA) to two radiation levels ("R" and "F") are provided for JANTXV and JANS product assurance levels.

1.2 Package outlines. The device package outlines are as follows: TO-276AC in accordance with [figure 1](#) for all encapsulated device types.

1.3 Maximum ratings.  $T_A = +25^\circ\text{C}$ , unless otherwise specified.

Type	$P_T$ (1) $T_C = +25^\circ\text{C}$	$P_T$ $T_A = +25^\circ\text{C}$	$R_{\theta JC}$ (2)	$V_{DS}$	$V_{DG}$	$V_{GS}$	$I_{D1}$ (3) (4) $T_C = +25^\circ\text{C}$	$I_{D2}$ $T_C = +100^\circ\text{C}$	$I_S$	$I_{DM}$ (5)	$T_J$ and $T_{STG}$
	<u>W</u>	<u>W</u>	<u>°C/W</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A (pk)</u>	<u>°C</u>
2N7579U2	250	1.56	0.5	100	100	±20	56	56	56	224	-55 to +150
2N7581U2	250	1.56	0.5	150	150	±20	56	49	56	224	
2N7583U2	250	1.56	0.5	200	200	±20	56	40	56	224	
2N7585U2	250	1.56	0.5	250	250	±20	50	31.5	50	200	

- (1) Derate linearly by 2.0 W/°C for  $T_C > +25^\circ\text{C}$ .
- (2) See [figure 2](#), thermal impedance curves.
- (3) The following formula derives the maximum theoretical  $I_D$  limit.  $I_D$  is limited to 56 A (by package and internal wires and may be limited by pin diameter):

$$I_D = \sqrt{\frac{T_{JM} - T_C}{(R_{\theta JC}) \times (R_{DS(on)} \text{ at } T_{JM})}}$$

- (4) See [figure 3](#), maximum drain current graph.
- (5)  $I_{DM} = 4 \times I_{D1}$ ;  $I_{D1}$  as calculated by footnote (3).

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1.4 Primary electrical characteristics at  $T_C = +25^\circ\text{C}$ .

Type	Min $V_{(BR)DSS}$ $V_{GS} = 0$ $I_D = 1.0\text{mA}$ dc	$V_{GS(TH)1}$ $V_{DS} \geq V_{GS}$ $I_D = 1.0\text{ mA}$ dc	Max $I_{DSS1}$ $V_{GS} = 0$ $V_{DS} = 80\%$  of rated $V_{DS}$	Max $r_{DS(on)}$ (1) $V_{GS} = 12\text{V}$ , $I_D = I_{D2}$		$V_{ISO}$ 70,000 ft. altitude	$E_{AS}$	
				$T_J = +25^\circ\text{C}$	$T_J = +150^\circ\text{C}$			
	<u>V dc</u>	<u>V dc</u> Min    Max		<u><math>\mu\text{A dc}</math></u>	<u><math>\Omega</math></u>	<u><math>\Omega</math></u>	<u>V dc</u>	<u>mJ</u>
2N7579U2	100	2.0	4.0	10	0.010	0.020		462
2N7581U2	150	2.0	4.0	10	0.018	0.0414		283
2N7583U2	200	2.0	4.0	10	0.028	0.063		268
2N7585U2	250	2.0	4.0	10	0.040	0.100	250	240

(1) Pulsed (see 4.5.1).

1.5 Part or Identifying Number (PIN). The PIN is in accordance with MIL-PRF-19500, and as specified herein. See 6.4 for PIN construction example and 6.5 for a list of available PINs.

1.5.1 JAN certification mark and quality level for encapsulated devices. The quality level designators for encapsulated devices that are applicable for this specification sheet from the lowest to the highest level are as follows: "JANTXV" and "JANS".

1.5.2 Radiation hardness assurance (RHA) designator. The RHA levels that are applicable for this specification sheet from lowest to highest are as follows: "R" and "F".

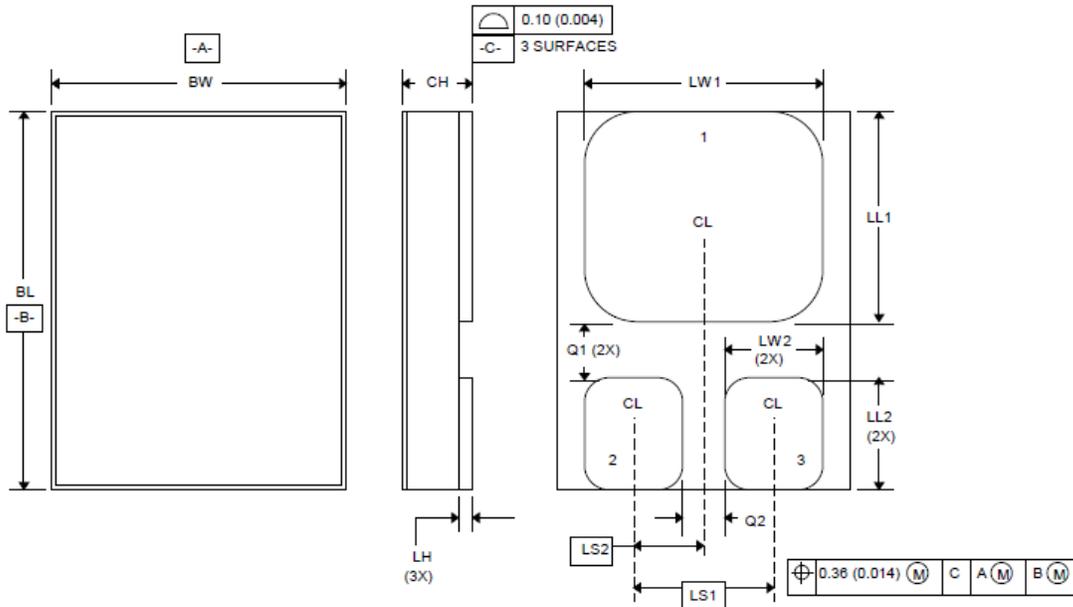
1.5.3 Device type. The designation system for the device types of transistors covered by this specification sheet are as follows.

1.5.3.1 First number and first letter symbols. The transistors of this specification sheet use the first number and letter symbols "2N".

1.5.3.2 Second number symbols. The second number symbols for the transistors covered by this specification sheet are as follows: "7579", "7581", "7583", and "7585".

1.5.3.3 Suffix letters. The suffix letters "U2" are used on devices that are packaged in the SMD2 TO-276AC package of figure 1.

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Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.685	.695	17.40	17.65
BW	.520	.530	13.21	13.46
CH		.142		3.60
LH	.010	.020	0.26	0.50
LW1	.435	.445	11.05	11.30
LW2	.135	.145	3.43	3.68
LL1	.470	.480	11.94	12.19
LL2	.152	.162	3.86	4.12
LS1	.240 BSC		6.10 BSC	
LS2	.120 BSC		3.05 BSC	
Q1	.035		0.89	
Q2	.050		1.27	
Term 1	Drain			
Term 2	Gate			
Term 3	Source			

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. In accordance with ASME Y14.5M, diameters are equivalent to  $\phi$ x symbology.
4. Terminal 1 – Drain, Terminal 2 – Gate, Terminal 3 – Source.

FIGURE 1. Physical dimensions for surface mount U2 (TO-276AC).

## 2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3 and 4 of this specification, whether or not they are listed.

### 2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

#### DEPARTMENT OF DEFENSE SPECIFICATIONS

[MIL-PRF-19500](#) - Semiconductor Devices, General Specification for.

#### DEPARTMENT OF DEFENSE STANDARDS

[MIL-STD-750](#) - Test Methods for Semiconductor Devices.

(Copies of these documents are available online at <http://quicksearch.dla.mil/>).

2.3 Order of precedence. Unless otherwise noted herein or in the contract, in the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

## 3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in [MIL-PRF-19500](#) and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see [4.2](#) and [6.3](#)).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in [MIL-PRF-19500](#).

3.4 Interface and physical dimensions. Interface and physical dimensions shall be as specified in [MIL-PRF-19500](#), and on [figure 1](#) (TO-276AC) herein.

3.4.1 Lead finish. Lead finish shall be solderable in accordance with [MIL-PRF-19500](#), [MIL-STD-750](#), and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see [6.2](#)).

3.4.2 Multiple chip construction. Multiple chip construction is not permitted to meet the requirements of this specification.

3.5 Electrostatic discharge (ESD) protection. The devices covered by this specification require electrostatic discharge protection (see [3.5.1](#)).

3.5.1 Handling. Metal oxide semiconductor (MOS) devices must be handled with certain precautions to avoid damage due to the accumulation of static charge. However, the following handling practices are recommended (see 3.5).

- a. Devices should be handled on benches with conductive handling devices.
- b. Ground test equipment, tools, and personnel handling devices.
- c. Do not handle devices by the leads.
- d. Store devices in conductive foam or carriers.
- e. Avoid use of plastic, rubber or silk in MOS areas.
- f. Maintain relative humidity above 50 percent if practical.
- g. Care should be exercised during test and troubleshooting to apply not more than maximum rated voltage to any lead.
- h. Gate must be terminated to source,  $R \leq$  or 100 k $\Omega$ , whenever bias voltage is applied drain to source.

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I.

3.7 Electrical test requirements. The electrical test requirements shall be as specified in table I.

3.8 Marking. Marking shall be in accordance with MIL-PRF-19500.

3.9 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

#### 4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4 and tables I and II).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500. Alternate flow is allowed for qualification inspection in accordance with MIL-PRF-19500.

4.2.1 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of table III tests, the tests specified in table III herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

4.2.1.1 Single event effects (SEE). SEE shall be performed at initial qualification and after process or design changes which may affect radiation hardness (see table III and table IV). Upon qualification, manufacturers shall provide the verification test conditions from section 5 of method 1080 of MIL-STD-750 that were used to qualify the device for inclusion into section 6 of the slash sheet. End-point measurements shall be in accordance with table II. SEE characterization data shall be made available upon request of the qualifying or acquiring activity.

4.3 Screening (JANS and JANTXV). Screening shall be in accordance with table E-IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table E-IV of MIL-PRF-19500) (1) (2)	Measurement	
	JANS	JANTXV
(3)	Gate stress test (see 4.3.1)	Gate stress test (see 4.3.1)
(3)	Method 3470 of MIL-STD-750, E <sub>AS</sub> (see 4.3.2)	Method 3470 of MIL-STD-750, E <sub>AS</sub> (see 4.3.2)
(3) 3c	Method 3161 of MIL-STD-750, thermal impedance, (see 4.3.3)	Method 3161 of MIL-STD-750, thermal impedance, (see 4.3.3)
9	Subgroup 2 of table I herein I <sub>GSSF1</sub> , I <sub>GSSR1</sub> , I <sub>DSS1</sub> as a minimum	Not applicable
10	Method 1042 of MIL-STD-750, test condition B	Method 1042 of MIL-STD-750, test condition B
11	I <sub>GSSF1</sub> , I <sub>GSSR1</sub> , I <sub>DSS1</sub> , r <sub>DS(ON)1</sub> , V <sub>GS(TH)1</sub> Subgroup 2 of table I herein. ΔI <sub>GSSF1</sub> = ±20 nA dc or ±100 percent of initial value, whichever is greater. ΔI <sub>GSSR1</sub> = ±20 nA dc or ±100 percent of initial value, whichever is greater. ΔI <sub>DSS1</sub> = ±10 μA dc or ±100 percent of initial value, whichever is greater.	I <sub>GSSF1</sub> , I <sub>GSSR1</sub> , I <sub>DSS1</sub> , r <sub>DS(ON)1</sub> , V <sub>GS(TH)1</sub> Subgroup 2 of table I herein.
12	Method 1042 of MIL-STD-750, test condition A	Method 1042 of MIL-STD-750, test condition A
13	Subgroups 2 and 3 of table I herein ΔI <sub>GSSF1</sub> = ±20 nA dc or ±100 percent of initial value, whichever is greater. ΔI <sub>GSSR1</sub> = ±20 nA dc or ±100 percent of initial value, whichever is greater. ΔI <sub>DSS1</sub> = ±10 μA dc or ±100 percent of initial value, whichever is greater. Δr <sub>DS(ON)1</sub> = ±20 percent of initial value. ΔV <sub>GS(TH)1</sub> = ±20 percent of initial value.	Subgroup 2 of table I herein ΔI <sub>GSSF1</sub> = ±20 nA dc or ±100 percent of initial value, whichever is greater. ΔI <sub>GSSR1</sub> = ±20 nA dc or ±100 percent of initial value, whichever is greater. ΔI <sub>DSS1</sub> = ±10 μA dc or ±100 percent of initial value, whichever is greater. Δr <sub>DS(ON)1</sub> = ±20 percent of initial value. ΔV <sub>GS(TH)1</sub> = ±20 percent of initial value.

- (1) At the end of the test program, I<sub>GSSF1</sub>, I<sub>GSSR1</sub>, and I<sub>DSS1</sub> are measured.
- (2) An out-of-family program to characterize I<sub>GSSF1</sub>, I<sub>GSSR1</sub>, I<sub>DSS1</sub>, V<sub>GS(th)1</sub>, and r<sub>DS(ON)1</sub> shall be invoked.
- (3) Shall be performed anytime after temperature cycling, screen 3a. JANTXV levels do not need to be repeated in screening requirements.

4.3.1 Gate stress test. Apply  $V_{GS} = 24$  V minimum for  $t = 250$   $\mu$ s minimum.

4.3.2 Single pulse avalanche energy ( $E_{AS}$ ).

- a. Peak current .....  $I_{AS} = I_{D1}$ .
- b. Inductance: .....  $\left[ \frac{2E_{AS}}{(I_{D1})^2} \right] \left[ \frac{V_{BR} - V_{DD}}{V_{BR}} \right]$  mH minimum.
- c. Gate to source resistor ( $R_{GS}$ ) .....  $25 \leq R_{GS} \leq 200$   $\Omega$ .
- d. Supply voltage ( $V_{DD}$ ) .....  $V_{DD} = 25$  V dc, except  $V_{DD} = 50$  V dc (2N7585U2), up to rated  $V_{DS}$ .
- e. Peak gate voltage ( $V_{GS}$ ) ..... 12 V, up to maximum rated  $V_{GS}$ .
- f. Initial case temperature .....  $T_C = +25^\circ\text{C} +10^\circ\text{C}, -5^\circ\text{C}$ .
- g. Number of pulses to be applied ..... 1 pulse minimum.

4.3.3 Thermal impedance. The thermal impedance measurements shall be performed in accordance with method 3161 of [MIL-STD-750](#) using the guidelines in that method for determining  $I_M$ ,  $I_H$ ,  $t_H$ ,  $t_{SW}$ , (and  $V_H$  where appropriate). See [table III](#), group E, subgroup 4 herein.

4.4 Conformance inspection. Conformance inspection shall be in accordance with [MIL-PRF-19500](#). Alternate flow is allowed for conformance inspection in accordance with [MIL-PRF-19500](#).

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with table V of [MIL-PRF-19500](#) and [table I](#) herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VIA (JANS) and table E-VIB (JANTXV) of [MIL-PRF-19500](#), and as follows.

4.4.2.1 Quality level JANS, table E-VIA of [MIL-PRF-19500](#).

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B3	1051	Test condition G, 100 cycles.
B4	1042	Intermittent operation life, condition D; $t_{on} = 30$ seconds minimum.
B5	1042	Accelerated steady-state gate bias, condition B, $V_{GS} = \text{rated}$ ; $T_A = +175^\circ\text{C}$ , $t = 24$ hours minimum; or $T_A = +150^\circ\text{C}$ , $t = 48$ hours minimum.
B5	1042	Accelerated steady-state reverse bias, condition A, $V_{DS} = \text{rated}$ ; $T_A = +175^\circ\text{C}$ , $t = 120$ hours minimum; or $T_A = +150^\circ\text{C}$ , $t = 240$ hours minimum.
B5	2037	Test condition D.

4.4.2.2 Quality level JANTXV, table E-VIB of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B2	1051	Test condition G, 25 cycles.
B3	1042	Intermittent operation life, condition D; $t_{on} = 30$ seconds minimum.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VII of MIL-PRF-19500 and as follows.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
C2	2036	Not applicable.
C5	3161	See 4.3.3, $R_{\theta JC} = 0.50$ °C/W.
C6	1042	Intermittent operation life, condition D; $t_{on} = 30$ seconds minimum.

4.4.4 Group D inspection. Group D inspection shall be conducted in accordance with table E-VIII of MIL-PRF-19500 and table II herein.

4.4.5 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-IX of MIL-PRF-19500 and as specified in table III herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

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TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Condition		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>						
Thermal impedance <u>2/</u>	3161	See 4.3.3	$Z_{\theta JC}$			°C/W
Breakdown voltage drain to source 2N7579U2 2N7581U2 2N7583U2 2N7585U2	3407	Bias condition C, $V_{GS} = 0$ V, $I_D = 1$ mA dc	$V_{(BR)DSS}$	100 150 200 250		V dc V dc V dc V dc
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$ , $I_D = 1$ mA dc	$V_{GS(TH)1}$	2.0	4.0	V dc
Gate current	3411	$V_{GS} = +20$ V dc, bias condition C, $V_{DS} = 0$ V	$I_{GSSF1}$		+100	nA dc
Gate current	3411	$V_{GS} = -20$ V dc, bias condition C, $V_{DS} = 0$ V	$I_{GSSR1}$		-100	nA dc
Drain current	3413	$V_{GS} = 0$ V dc, bias condition C, $V_{DS} = 80$ percent of rated $V_{DS}$	$I_{DSS1}$		10	μA dc
Static drain to source on-state resistance 2N7579U2 2N7581U2 2N7583U2 2N7585U2	3421	$V_{GS} = 12$ V dc, condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(ON)1}$		0.010 0.018 0.028 0.040	Ω Ω Ω Ω
Forward voltage	4011	$V_{GS} = 0$ V dc, condition A, pulsed (see 4.5.1), $I_D = I_{D1}$	$V_{SD}$		1.2	V dc

See footnotes at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Condition		Min	Max	
<u>Subgroup 3</u>						
High temperature operation						
$T_C = T_J = +125^\circ\text{C}$						
Gate current	3411	$V_{GS} = \pm 20\text{ V dc}$ , bias condition C, $V_{DS} = 0\text{ V}$	$I_{GSS2}$		$\pm 200$	nA dc
Drain current	3413	$V_{GS} = 0\text{ V dc}$ , bias condition C, $V_{DS} = 80\text{ percent of rated } V_{DS}$	$I_{DSS2}$		25	$\mu\text{A dc}$
Static drain to source on-state resistance	3421	$V_{GS} = 12\text{ V dc}$ , condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(ON)3}$			
2N7579U2					0.018	$\Omega$
2N7581U2					0.036	$\Omega$
2N7583U2					0.056	$\Omega$
2N7585U2					0.088	$\Omega$
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$ , $I_D = 1\text{ mA dc}$	$V_{GS(TH)2}$	1.0		V dc
Low temperature operation						
$T_C = T_J = -55^\circ\text{C}$						
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS(TH)3}$ , $I_D = 1\text{ mA dc}$	$V_{GS(TH)3}$		5.0	V dc
<u>Subgroup 4</u>						
Forward transconductance	3475	$I_D = I_{D2}$ , $V_{DD} = 15\text{ V dc}$ (see 4.5.1)	$g_{FS}$			
2N7579U2				60		S
2N7581U2				50		S
2N7583U2				40		S
2N7585U2				37		S
Switching time test	3472	$I_D = \text{rated } I_{D1}$ , $V_{GS} = -12\text{ V dc}$ , $R_G = 2.35\ \Omega$ (U2), $V_{DD} = 50\text{ percent of rated } V_{DS}$				
Turn-on delay time			$t_d(\text{on})$		50	ns
Rise time			$t_r$		150	ns
Turn-off delay time			$t_d(\text{off})$		100	ns
Fall time			$t_f$		50	ns

See footnotes at end of table.

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TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Condition		Min	Max	
<u>Subgroup 5</u> Safe operating area test (high voltage)	3474	$V_{DS} = 80$ percent of rated $V_{DS}$ (see <a href="#">1.3</a> ), $t_p = 10$ ms, $I_D$ as specified on <a href="#">figure 4</a>				
<u>Subgroup 6</u> Not applicable						
<u>Subgroup 7</u> Gate charge	3471	Condition B, $I_D = I_{D1}$ , $V_{GS} = 12$ V dc $V_{DD} = 50$ percent of rated $V_{DS}$				
On-state gate charge (turn-on and turn-off) 2N7579U2			$Q_{G(ON)}$ $Q_{G(OFF)}$		170	nC
2N7581U2					230	nC
2N7583U2					240	nC
2N7585U2					220	nC
Gate to source charge (turn-on and turn-off) 2N7579U2			$Q_{GS1}$ $Q_{GS2}$		60	nC
2N7581U2					70	nC
2N7583U2					70	nC
2N7585U2					50	nC
Gate to drain charge (turn-on and turn-off) 2N7579U2			$Q_{GD1}$ $Q_{GD2}$		80	nC
2N7581U2					90	nC
2N7583U2					60	nC
2N7585U2					70	nC
Reverse recovery time	3473	$di/dt = -100$ A/ $\mu$ s, $V_{DD} \leq 50$ V $I_D = I_{D1}$	$t_{rr}$			
2N7579U2					500	ns
2N7581U2					370	ns
2N7583U2					640	ns
2N7585U2					700	ns

1/ For sampling plan, see [MIL-PRF-19500](#).

2/ This test required for the following end-point measurements only:

Group B, subgroups 2 and 3 (JANTXV).

Group B, subgroups 3 and 4 (JANS).

Group C, subgroup 2 and 6.

Group E, subgroup 1.

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TABLE II. Group D inspection.

Inspection <u>1/ 2/ 3/</u>	MIL-STD-750		Symbol	Pre-irradiation limits		Post-irradiation limits		Unit
	Method	Conditions		R and F		R and F		
				Min	Max	Min	Max	
<u>Subgroup 1</u>								
Not applicable								
<u>Subgroup 2</u>		$T_C = + 25^\circ\text{C}$						
Steady-state total dose irradiation ( $V_{GS}$ bias) <u>4/</u>	1019	$V_{GS} = 12 \text{ V};$ $V_{DS} = 0$						
Steady-state total dose irradiation ( $V_{DS}$ bias) <u>4/</u>	1019	$V_{GS} = 0; V_{DS} = 80$ percent of rated $V_{DS}$ (pre-irradiation)						
End-point electricals:								
Breakdown voltage, drain to source 2N7579U2 2N7581U2 2N7583U2 2N7585U2	3407	Bias condition C, $V_{GS} = 0; I_D = 1 \text{ mA}$	$V_{(BR)DSS}$	100 150 200 250		100 150 200 250		V dc V dc V dc V dc
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$ $I_D = 1 \text{ mA}$	$V_{GS(th)1}$	2.0	4.0	2.0	4.0	V dc
Gate current	3411	Bias condition C, $V_{GS} = +20 \text{ V}; V_{DS} = 0$	$I_{GSSF1}$		100		100	nA dc
Gate current	3411	Bias condition C, $V_{GS} = -20 \text{ V}; V_{DS} = 0$	$I_{GSSR1}$		-100		-100	nA dc
Drain current	3413	Bias condition C, $V_{GS} = 0$ $V_{DS} = 80$ percent of rated $V_{DS}$ (pre-irradiation)	$I_{DSS}$		10		10	$\mu\text{A}$ dc
Static drain to source on-state voltage 2N7579U2 2N7581U2 2N7583U2 2N7585U2	3405	$V_{GS} = 12 \text{ V}; I_D = I_{D2}$ condition A, pulsed (see <a href="#">4.5.1</a> )	$V_{DS(on)}$		0.616 0.931 1.160 1.291		0.616 0.931 1.160 1.291	V dc V dc V dc V dc
Forward voltage source drain diode	4011	Bias condition C, $V_{GS} = 0; I_D = I_{D1}$	$V_{SD}$		1.2		1.2	V dc

1/ For sampling plan see [MIL-PRF-19500](#).

2/ Group D qualification may be performed prior to lot formation. Wafers qualified to these group D QCI requirements may be used for any other specification sheets utilizing the same die design.

3/ At the manufacturer's option, group D samples need not be subjected to the screening tests, and may be assembled in its qualified package or in any qualified package that the manufacturer has data to correlate the performance to the designated package.

4/ Separate samples shall be pulled for each bias.

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TABLE III. Group E inspection (all quality levels) for qualification or re-qualification only.

Inspection	MIL-STD-750		Sample plan
	Method	Conditions	
<u>Subgroup 1</u>			45 devices c = 0
Temperature cycling	1051	-55°C to +150°C, 500 cycles	
Hermetic seal Fine leak Gross leak	1071	As applicable.	
Electrical measurements		See <a href="#">table I</a> , subgroup 2 herein.	
<u>Subgroup 2 1/</u>			45 devices c = 0
Steady-state gate bias	1042	Condition B, 1,000 hours.	
Electrical measurements		See <a href="#">table I</a> , subgroup 2 herein.	
Steady-state reverse bias	1042	Condition A, 1,000 hours.	
Electrical measurements		See <a href="#">table I</a> , subgroup 2 herein.	
<u>Subgroup 4</u>			Sample size N/A
Thermal impedance curves		See <a href="#">MIL-PRF-19500</a> .	
<u>Subgroup 5</u>			3 devices c = 0
Barometric pressure 2N7585U2 only	1001	To 70,000 feet	
<u>Subgroup 10</u>			22 devices c = 0
Commutating diode for safe operating area test procedure for measuring dv/dt during reverse recovery of power MOSFET transistors or insulated gate bipolar transistors	3476	Test conditions shall be derived by the manufacturer	
<u>Subgroup 11</u>			
SEE <a href="#">2/</a> <a href="#">3/</a>			

[1/](#) A separate sample for each test shall be pulled.

[2/](#) Group E qualification of SEE testing may be performed prior to lot formation. Qualification may be extended to other specification sheets utilizing the same structurally identical die design.

[3/](#) Device qualification to a higher level linear energy transfer (LET) is sufficient to qualify all lower level LETs.

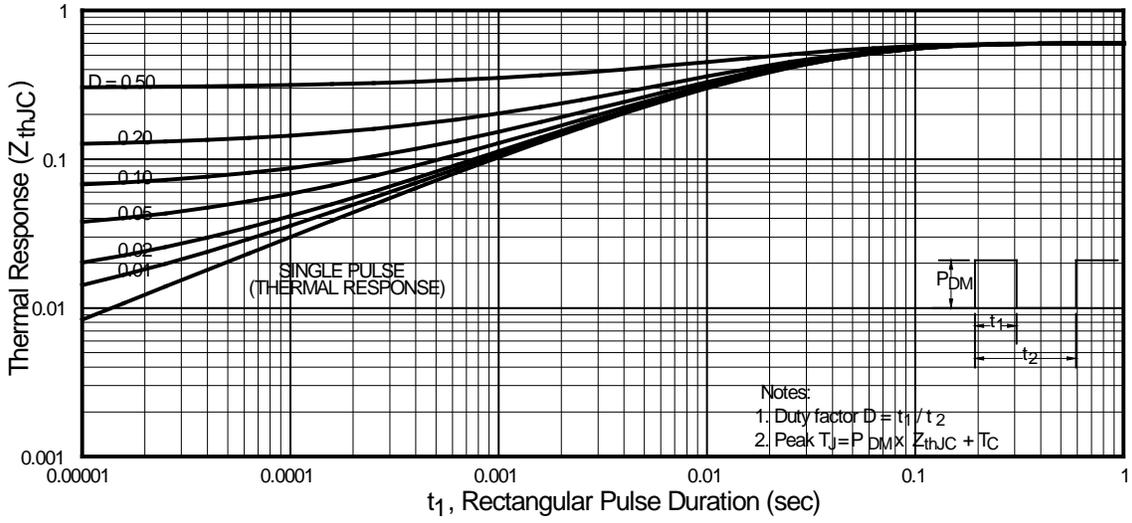


FIGURE 2. Thermal impedance curve.

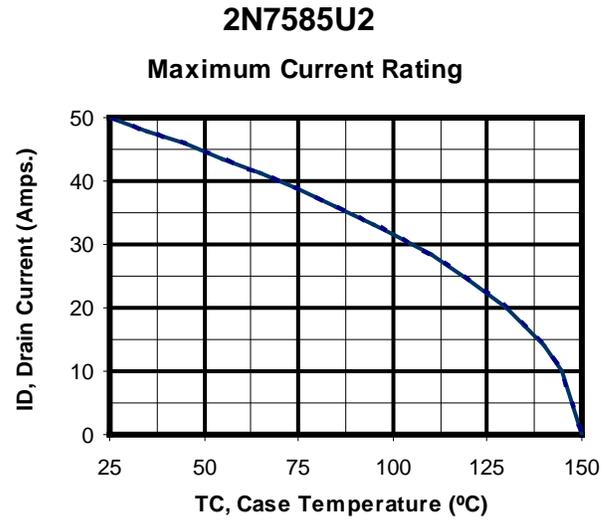
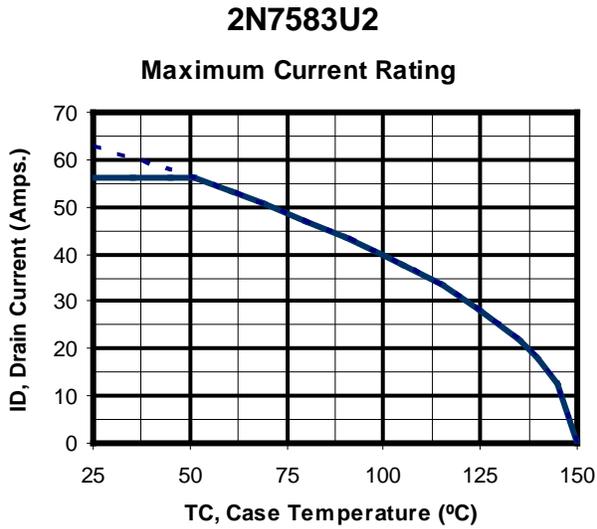
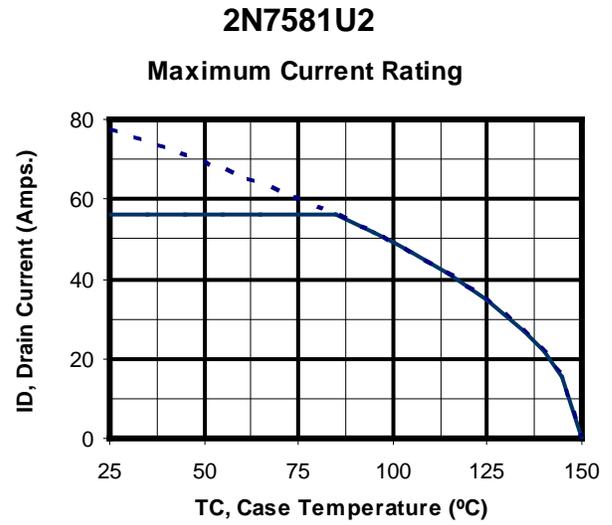
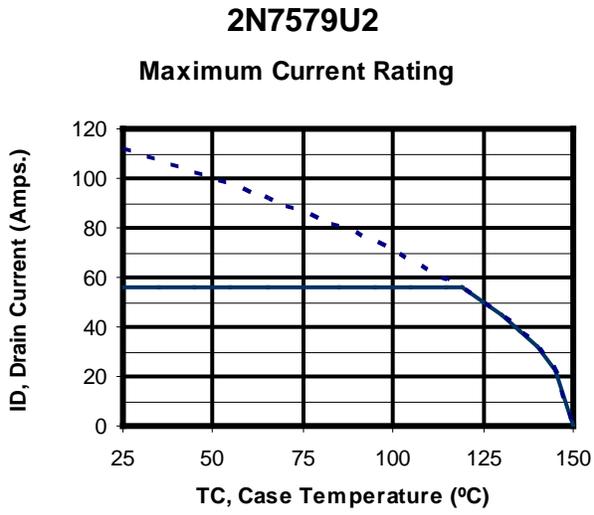


FIGURE 3. Maximum drain current versus case temperature graphs.

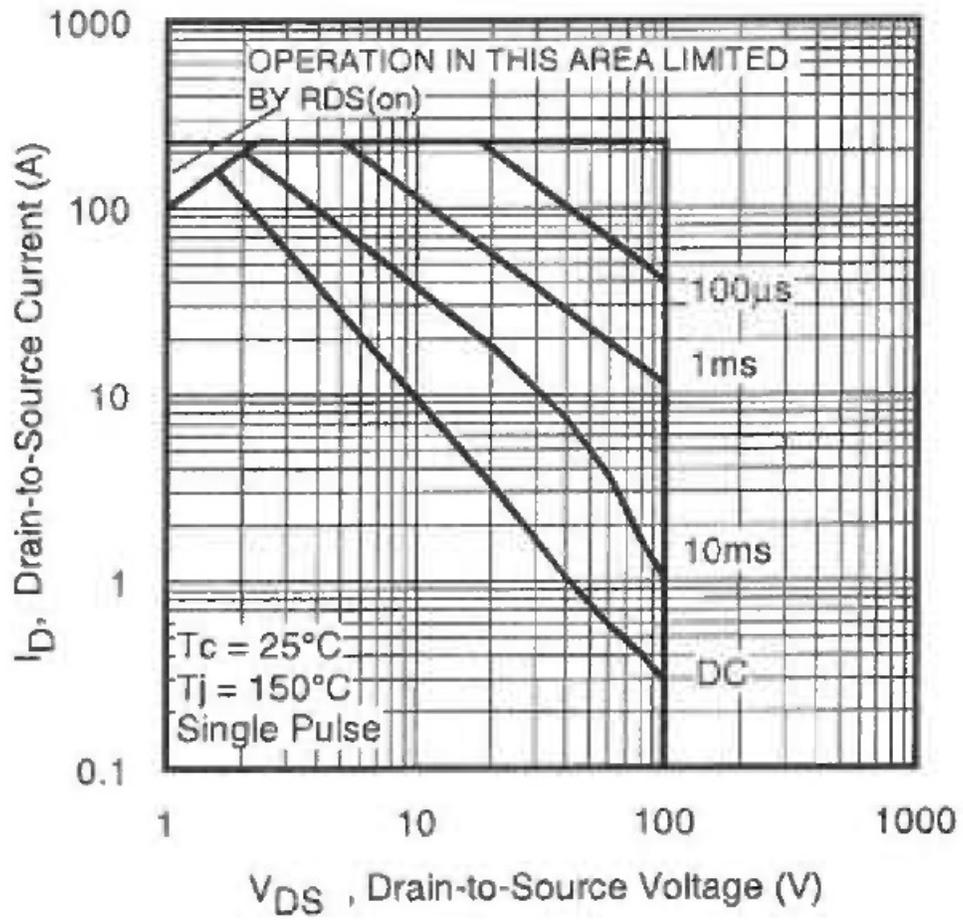


FIGURE 4. Safe operating area graph.

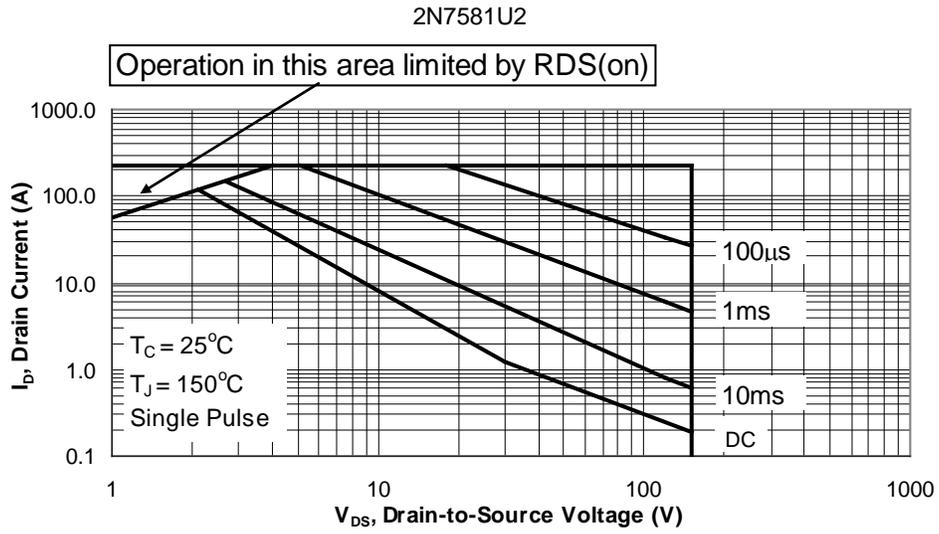
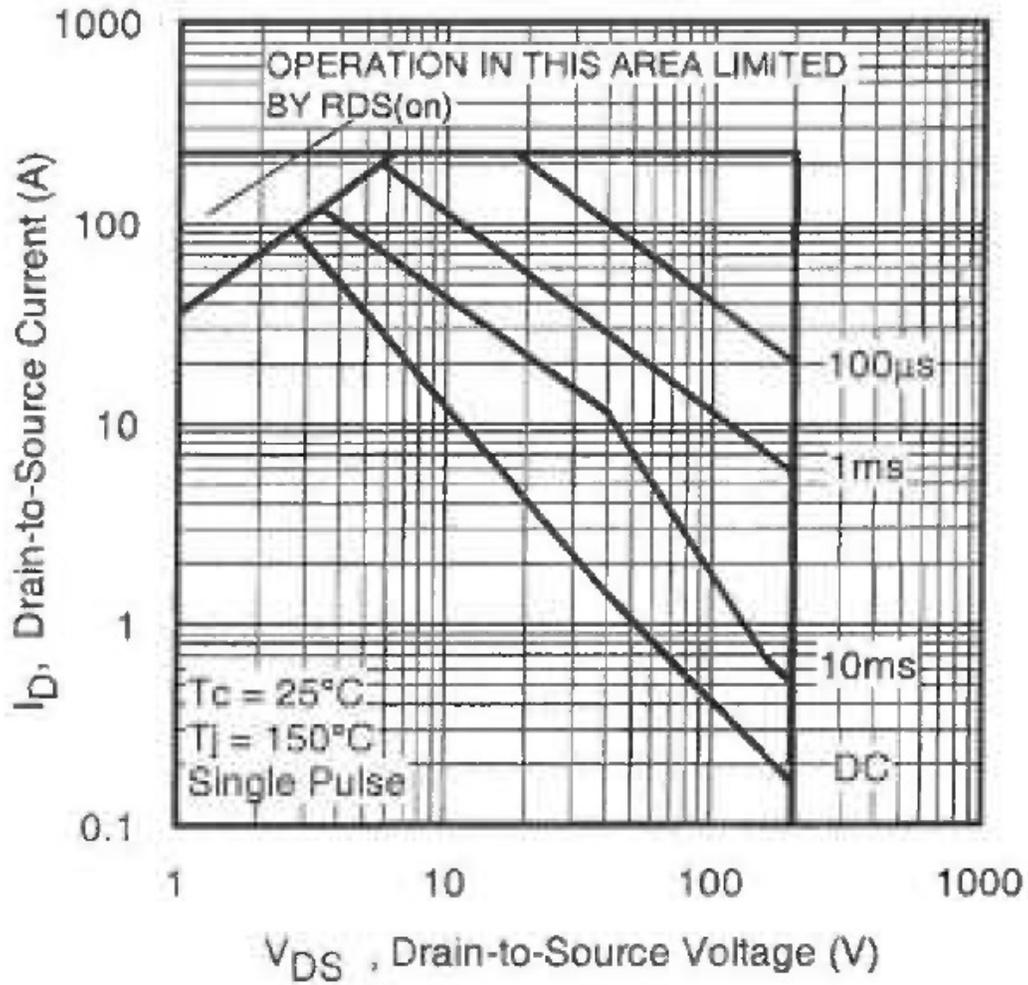


FIGURE 4. Safe operating area graph - Continued.



2N7583U2

FIGURE 4. Safe operating area graph - Continued.

2N7585U2

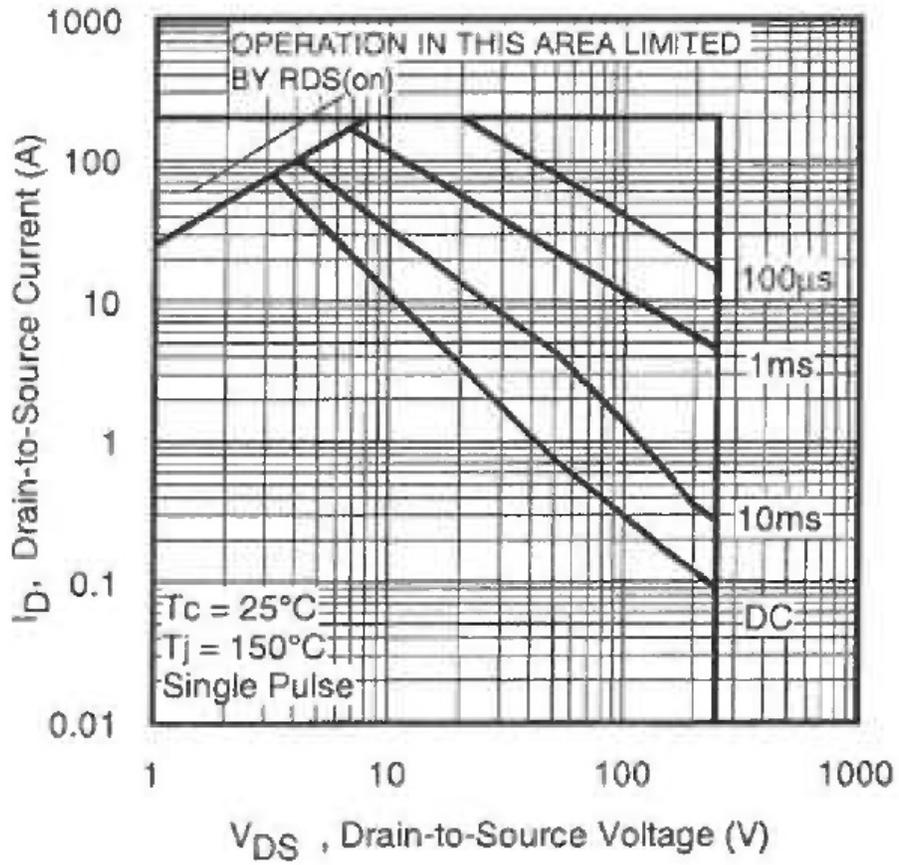


FIGURE 4. Safe operating area graph - Continued.

## 5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

## 6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in [MIL-PRF-19500](#) are applicable to this specification.)

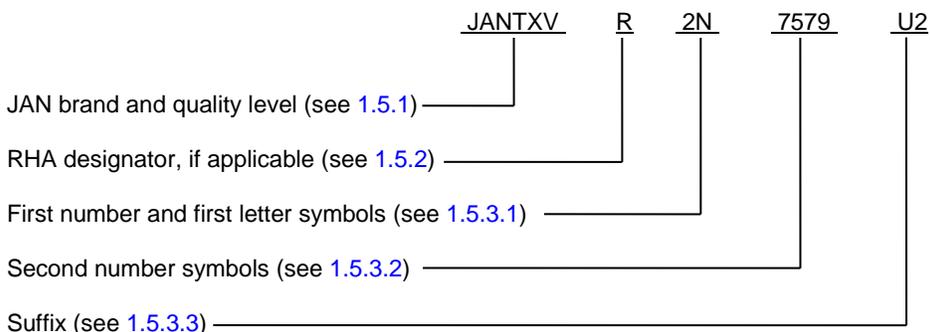
6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see 3.4.1).
- d. The complete PIN, see 1.5 and 6.5.
- e. For acquisition of RHA designated devices, [table II](#), subgroup 1 testing of group D herein is optional. If subgroup 1 is desired, it should be specified in the contract or order.
- f. If SEE testing data is desired, it should be specified in the contract or order.
- g. If specific SEE characterization conditions are desired (see section 6.7 and [table IV](#)), manufacturer's cage code should be specified in the contract or order.

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DLA Land and Maritime, ATTN: VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail [vqe.chief@dla.mil](mailto:vqe.chief@dla.mil). An online listing of products qualified to this specification may be found in the Qualified Products Database (QPD) at <https://assist.dla.mil>.

6.4 PIN construction example. The PINs for encapsulated devices are construction using the following form.



6.5 List of PINs. The following is a list of possible PINs available on this specification sheet.

PINs for devices of the "TXV" quality level	PINs for devices of the "TXV" quality level with RHA (1)	PINs for devices of the "S" quality level	PINs for devices of the "S" quality level with RHA (1)
JANTXV2N7579U2	JANTXV#2N7579U2	JANS2N7579U2	JANS#2N7579U2
JANTXV2N7581U2	JANTXV#2N7581U2	JANS2N7581U2	JANS#2N7581U2
JANTXV2N7583U2	JANTXV#2N7583U2	JANS2N7583U2	JANS#2N7583U2
JANTXV2N7585U2	JANTXV#2N7585U2	JANS2N7585U2	JANS#2N7585U2

(1) The number sign (#) represent one of two RHA designators available on this specification sheet ("R" or "F").

6.6 Substitution information. Devices covered by this specification are substitutable for the manufacturer's and user's Part or Identifying Number (PIN) (without JAN and RHA prefix). This information in no way implies that manufacturer's PINs are substitutable for the military PIN.

Preferred types military PIN	Commercial PIN
2N7579U2	IRHNA67160
2N7581U2	IRHNA67164
2N7583U2	IRHNA67260
2N7585U2	IRHNA67264

6.7 Application data.

6.7.1 Manufacturer specific irradiation data. Each manufacturer qualified to this slash sheet has characterized its devices to the requirements of MIL-STD-750 method 1080 and as specified herein. Since each manufacturer's characterization conditions can be different and can vary by the version of method 1080 qualified to, the MIL-STD-750 method 1080 revision version date and conditions used by each manufacturer for characterization have been listed here (see table IV) for information only. SEE conditions and figures listed in section 6 are current as of the date of this specification sheet, please contact the manufacturer for the most recent conditions.

TABLE IV. Manufacturers characterization conditions.

Manufactures cage	Inspection	MIL-STD-750		Sample plan
		Method	Conditions	
69210 (Applicable to devices with a date code of March 2011 and older)	SEE <u>1/</u>	1080	See MIL-STD-750E method 1080.0 dated 20 November 2006. See figure 5	3 devices
	Electrical measurements		$I_{GSSF1}$ , $I_{GSSR1}$ , and $I_{DSS1}$ in accordance with table I, subgroup 2	
	SEE irradiation:		Fluence = $3E5 \pm 20$ percent ions/cm <sup>2</sup> Flux = $2E3$ to $2E4$ ions/cm <sup>2</sup> /sec, temperature = $25^\circ \pm 5$ °C	
	2N7579U2		Surface LET = 39 MeV-cm <sup>2</sup> /mg $\pm 5\%$ , range = 40 $\mu\text{m} \pm 7.5\%$ , energy = 315 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 100$ V and $V_{GS} = -19$ V; $V_{DS} = 40$ V and $V_{GS} = -20$ V (typical 3.80 MeV/nucleon at Texas A & M Cyclotron)	
	2N7581U2		Surface LET = 39 MeV-cm <sup>2</sup> /mg $\pm 5\%$ , range = 50 $\mu\text{m} \pm 5\%$ , energy = 410 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 150$ V and $V_{GS} = -20$ V (typical 4.90 MeV/nucleon at Texas A & M Cyclotron)	
	2N7583U2		Surface LET = 42 MeV-cm <sup>2</sup> /mg $\pm 5\%$ , range = 205 $\mu\text{m} \pm 5\%$ , energy = 2450 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 200$ V and $V_{GS} = -10$ V; $V_{DS} = 190$ V and $V_{GS} = -15$ V (typical 8.49 MeV/nucleon at Texas A & M Cyclotron)	
	2N7585U2		Surface LET = 44 MeV-cm <sup>2</sup> /mg $\pm 5\%$ , range = 125 $\mu\text{m} \pm 10\%$ , energy = 1350 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 250$ V and $V_{GS} = -15$ V ; $V_{DS} = 40$ V and $V_{GS} = -20$ V (typical 10.05 MeV/nucleon at Texas A & M Cyclotron)	
	2N7579U2		Surface LET = 61 MeV-cm <sup>2</sup> /mg $\pm 5\%$ , range = 32 $\mu\text{m} \pm 7.5\%$ , energy = 345 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 100$ V and $V_{GS} = -10$ V; $V_{DS} = 30$ V and $V_{GS} = -15$ V (typical 2.70 MeV/nucleon at Texas A & M Cyclotron)	
	2N7581U2		Surface LET = 61 MeV-cm <sup>2</sup> /mg $\pm 5\%$ , range = 66 $\mu\text{m} \pm 7.5\%$ , energy = 825 MeV $\pm 5\%$ In-situ bias conditions: $V_{DS} = 150$ V and $V_{GS} = -10$ V; $V_{DS} = 40$ V and $V_{GS} = -15$ V (typical 6.40 MeV/nucleon at Texas A & M Cyclotron)	

TABLE IV. Manufacturers characterization conditions- Continued

Manufactures cage	Inspection	MIL-STD-750		Sample plan
		Method	Conditions	
	2N7583U2		Surface LET = 61 MeV- cm <sup>2</sup> /mg ±5%, range = 66 μm ±7.5%, energy = 825 MeV ±5% In-situ bias conditions: V <sub>DS</sub> = 200 V and V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 190 V and V <sub>GS</sub> = -15 V (typical 6.41 MeV/nucleon at Texas A & M Cyclotron)	
	2N7585U2		Surface LET = 61 MeV- cm <sup>2</sup> /mg ±5%, range = 66 μm ±7.5%, energy = 825 MeV ±5% In-situ bias conditions: V <sub>DS</sub> = 250 V and V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 50 V and V <sub>GS</sub> = -15 V (typical 6.41 MeV/nucleon at Texas A & M Cyclotron)	
	2N7579U2		Surface LET = 90 MeV- cm <sup>2</sup> /mg ±5%, range = 29 μm ±7.5%, energy = 375 MeV ±7.5% In-situ bias conditions: V <sub>DS</sub> = 100 V and V <sub>GS</sub> = -5 V (typical 1.88 MeV/nucleon at Texas A & M Cyclotron)	
	2N7581U2		Surface LET = 90 MeV- cm <sup>2</sup> /mg ±5%, range = 80 μm ±5%, energy = 1470 MeV ±5% In-situ bias conditions: V <sub>DS</sub> = 50 V and V <sub>GS</sub> = -5 V; V <sub>DS</sub> = 30 V and V <sub>GS</sub> = -10 V (typical 7.47 MeV/nucleon at Texas A & M Cyclotron)	
	2N7583U2		Surface LET = 90 MeV- cm <sup>2</sup> /mg ±5%, range = 80 μm ±5%, energy = 1470 MeV ±5% In-situ bias conditions: V <sub>DS</sub> = 170 V and V <sub>GS</sub> = -5 V (typical 7.47 MeV/nucleon at Texas A & M Cyclotron)	
	2N7585U2		Surface LET = 90 MeV- cm <sup>2</sup> /mg ±5%, range = 80 μm ±5%, energy = 1470 MeV ±5% In-situ bias conditions: V <sub>DS</sub> = 75 V and V <sub>GS</sub> = -5 V (typical 7.47 MeV/nucleon at Texas A & M Cyclotron)	
	Electrical measurements		I <sub>GSSF1</sub> , I <sub>GSSR1</sub> , and I <sub>DSS1</sub> in accordance with <a href="#">table I</a> , subgroup 2	
<div style="border: 1px solid black; padding: 5px; width: fit-content; margin: 0 auto;">                     Upon qualification, all manufacturers should provide the verification test conditions to be added to this table.                 </div>				

1/ I<sub>GSSF1</sub>, I<sub>GSSR1</sub>, and I<sub>DSS1</sub> was examined before and following SEE irradiation to determine acceptability for each bias condition. Other test conditions in accordance with [table I](#), subgroup 2, may be performed at the manufacturer's option.

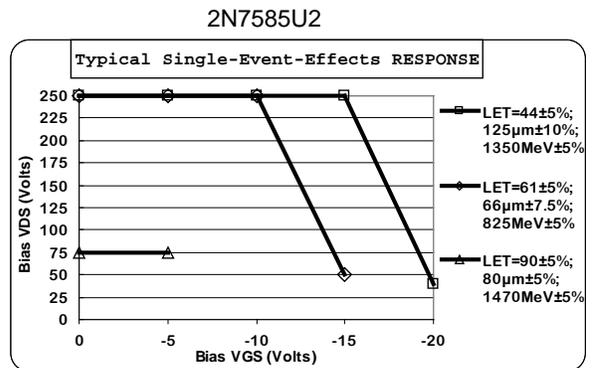
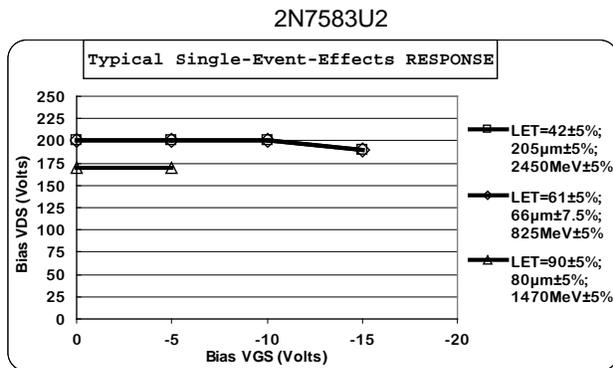
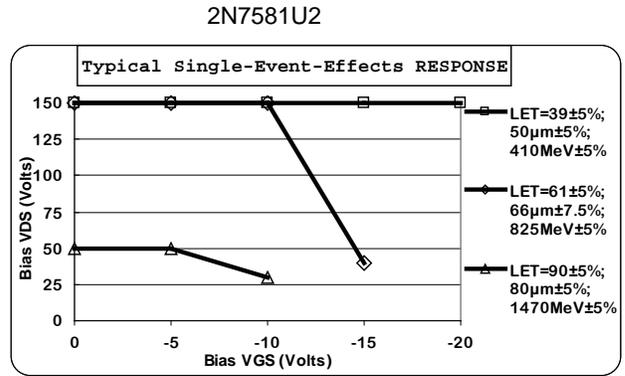
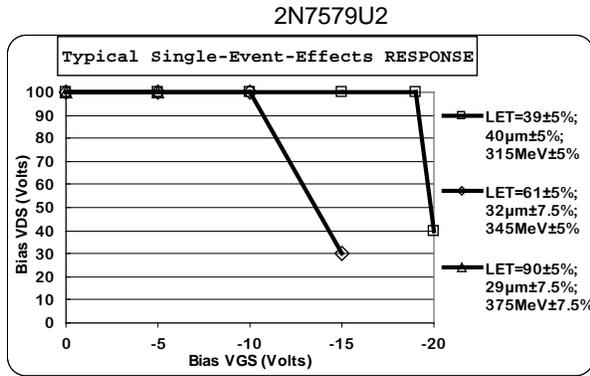


FIGURE 5. SEE safe operating area graph.

6.8 Request for new types and configurations. Requests for new device types or configurations for inclusions in this specification sheet should be submitted to: DLA Land and Maritime, ATTN: VAC, Post Office Box 3990, Columbus, OH 43218-3990 or by electronic mail at [Semiconductor@dla.mil](mailto:Semiconductor@dla.mil) or by facsimile (614) 693-1642 or DSN 850-6939.

6.9 Changes from previous issue. Marginal notations are not used in this revision to identify changes with respect to the previous issue due to the extent of the changes.

Custodians:

Army - CR  
Navy - EC  
Air Force - 85  
NASA - NA  
DLA - CC

Preparing activity:  
DLA - CC

(Project 5961-2016-045)

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.dla.mil>.